

CLAIM LISTING:

Claims 1-21 (canceled)

22. (original) A method of fabricating a flash memory device, said flash memory device comprising a silicon substrate, a first electrode of polysilicon formed on said silicon substrate with an insulation film interposed therebetween, and a second electrode formed on said first electrode with an inter-electrode oxynitride film interposed therebetween,

characterized in that said inter-electrode oxynitride film being formed by a process comprising the steps of:

depositing a polysilicon film on said silicon substrate as said first electrode;

and

converting a surface of said polysilicon film to a silicon oxynitride film by exposing said polysilicon film to plasma formed by exciting a mixed gas on an inert gas predominantly of Ar or Kr and a gas containing oxygen and nitrogen by a microwave.

Claims 23-51 (canceled)